

## isc N-Channel MOSFET Transistor

## IXTH60N20L2

### • FEATURES

- With TO-247 packaging
- · High speed switching
- · Very high commutation ruggedness
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



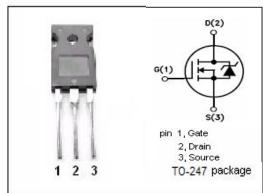
- PFC stages
- Power supply
- · Switching applications

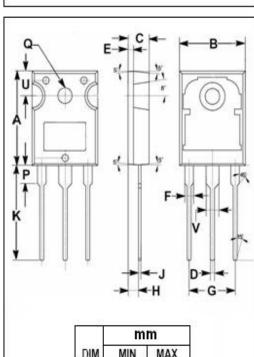


ABOOLOTE IIII BRITISHI TURTINGO(Ta 200)						
PARAMETER	VALUE	UNIT				
Drain-Source Voltage	200	V				
Gate-Source Voltage	±30	V				
Drain Current-Continuous	60	А				
Drain Current-Single Pulsed	150	А				
Total Dissipation	540	W				
Operating Junction Temperature	-55~150	$^{\circ}$				
Storage Temperature	-55~150	$^{\circ}$				
	PARAMETER  Drain-Source Voltage  Gate-Source Voltage  Drain Current-Continuous  Drain Current-Single Pulsed  Total Dissipation  Operating Junction Temperature	PARAMETER       VALUE         Drain-Source Voltage       200         Gate-Source Voltage       ±30         Drain Current-Continuous       60         Drain Current-Single Pulsed       150         Total Dissipation       540         Operating Junction Temperature       -55~150				

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.23	°C/W





	mm		
DIM	MIN	MAX	
Α	19.80	20.20	
В	15.40	15.80	
C	4.90	5.10	
D	0.90	1.10	
E	1.40	1.60	
F	1.90	2.10	
G	10.80	11.00	
Н	2.40	2.60	
J	0.50	0.70	
K	19.50	20.50	
P	3.90	4.10	
Q	3.30	3.50	
U	5.20	5.40	
V	2.90	3.10	



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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 1mA	200			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.25mA	2.5		4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =30A			45	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V			±0.1	μ <b> A</b>
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 200V; V <sub>GS</sub> = 0V;Tc=25°C V <sub>DS</sub> = 200V; V <sub>GS</sub> = 0V;Tc=125°C			5 50	μ <b>А</b>
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =60A, V <sub>GS</sub> = 0 V			1.4	V

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